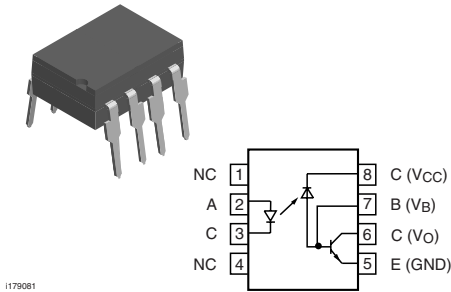


# High Speed Optocoupler, 1 MBd, Phtodiode with Transistor Output



## DESCRIPTION

The 6N135 and 6N136 are optocouplers with a GaAlAs infrared emitting diode, optically coupled with an integrated photo detector which consists of a photo diode and a high-speed transistor in a DIP-8 plastic package. Signals can be transmitted between two electrically separated circuits up to frequencies of 2.0 MHz. The potential difference between the circuits to be coupled should not exceed the maximum permissible reference voltages.

## FEATURES

- Isolation test voltages: 5300 V<sub>RMS</sub>
- TTL compatible
- High bit rates: 1.0 Mbit/s
- High common-mode interference immunity
- Bandwidth 2.0 MHz
- Open-collector output
- External base wiring possible
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS COMPLIANT

## AGENCY APPROVALS

- UL1577, file no. E52744 system code H or J, double protection
- DIN EN 60747-5-5 available with option 1
- CSA 93751

ORDER INFORMATION	
PART	REMARKS
6N135	CTR ≥ 7 %, DIP-8
6N136	CTR ≥ 19 %, DIP-8
6N135-X007	CTR ≥ 7 %, SMD-8 (option 7)
6N136-X006	CTR ≥ 19 %, DIP-8 400 mil (option 6)
6N136-X007	CTR ≥ 19 %, SMD-8 (option 7)
6N136-X009	CTR ≥ 19 %, SMD-8 (option 9)

### Note

For additional information on the available options refer to option information.

ABSOLUTE MAXIMUM RATINGS (1)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
<b>INPUT</b>				
Reverse voltage		V <sub>R</sub>	5.0	V
Forward current		I <sub>F</sub>	25	mA
Peak forward current	t = 1.0 ms, duty cycle 50 %	I <sub>FSM</sub>	50	mA
Maximum surge forward current	t ≤ 1.0 μs, 300 pulses/s		1.0	A
Thermal resistance		R <sub>th</sub>	700	K/W
Power dissipation	T <sub>amb</sub> = 70 °C	P <sub>diss</sub>	45	mW
<b>OUTPUT</b>				
Supply voltage		V <sub>S</sub>	- 0.5 to 15	V
Output voltage		V <sub>O</sub>	- 0.5 to 15	V
Emitter base voltage		V <sub>EBO</sub>	5.0	V
Output current		I <sub>O</sub>	8.0	mA
Maximum Output current			16	mA
Base current		I <sub>B</sub>	5.0	mA
Thermal resistance			300	K/W
Power dissipation	T <sub>amb</sub> = 70 °C	P <sub>diss</sub>	100	mW



ABSOLUTE MAXIMUM RATINGS <sup>(1)</sup>				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
<b>COUPLER</b>				
Isolation test voltage (between emitter and detector climate per DIN 50014 part 2, Nov. 74)	t = 1.0 s	V <sub>ISO</sub>	5300	V <sub>RMS</sub>
Pollution degree (DIN VDE 0109)			2.0	
Isolation resistance	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 25 °C	R <sub>IO</sub>	≥ 10 <sup>12</sup>	Ω
	V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 100 °C	R <sub>IO</sub>	≥ 10 <sup>11</sup>	Ω
Storage temperature range		T <sub>stg</sub>	- 55 to + 125	°C
Ambient temperature range		T <sub>amb</sub>	- 55 to + 100	°C
Soldering temperature <sup>(2)</sup>	max. ≤ 10 s, dip soldering ≥ 0.5 mm from case bottom	T <sub>slid</sub>	260	°C

**Notes**

- <sup>(1)</sup> T<sub>amb</sub> = 25 °C, unless otherwise specified. Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.
- <sup>(2)</sup> Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

ELECTRICAL CHARACTERISTICS <sup>(1)</sup>							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
<b>INPUT</b>							
Forward voltage	I <sub>F</sub> = 1.6 mA		V <sub>F</sub>		1.6	1.9	V
Breakdown voltage	I <sub>R</sub> = 10 μA		V <sub>BR</sub>	5.0			V
Reverse current	V <sub>R</sub> = 5.0 V		I <sub>R</sub>		0.5	10	μA
Capacitance	V <sub>R</sub> = 0 V, f = 1.0 MHz		C <sub>O</sub>		125		pF
Temperature coefficient, forward voltage	I <sub>F</sub> = 1.6 mA		ΔV <sub>F</sub> /ΔT <sub>A</sub>		- 1.7		mV/°C
<b>OUTPUT</b>							
Logic low supply current	I <sub>F</sub> = 1.6 mA, V <sub>O</sub> = open, V <sub>CC</sub> = 15 V		I <sub>CCL</sub>		150		μA
Logic high supply current	I <sub>F</sub> = 0 mA, V <sub>O</sub> = open, V <sub>CC</sub> = 15 V		I <sub>CCH</sub>		0.01	1	μA
Output voltage, output low	I <sub>F</sub> = 16 mA, I <sub>O</sub> = 1.1 mA, V <sub>CC</sub> = 4.5 V	6N135	V <sub>OL</sub>		0.1	0.4	V
	I <sub>F</sub> = 16 mA, I <sub>O</sub> = 2.4 mA, V <sub>CC</sub> = 4.5 V	6N136	V <sub>OL</sub>		0.1	0.4	V
Output current, output high	I <sub>F</sub> = 0 mA, V <sub>O</sub> = V <sub>CC</sub> = 5.5 V		I <sub>OH</sub>		3.0	500	nA
	I <sub>F</sub> = 0 mA, V <sub>O</sub> = V <sub>CC</sub> = 15 V		I <sub>OH</sub>		0.01	1	μA
<b>COUPLER</b>							
Capacitance (input to output)	f = 1.0 MHz		C <sub>IO</sub>		0.6		pF

**Note**

T<sub>amb</sub> = 25 °C, unless otherwise specified. Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Current transfer ratio	$I_F = 16 \text{ mA}$ , $V_O = 0.4 \text{ V}$ , $V_{CC} = 4.5 \text{ V}$	6N135	CTR	7	16		%
		6N136	CTR	19	35		%
	$I_F = 16 \text{ mA}$ , $V_O = 0.5 \text{ V}$ , $V_{CC} = 4.5 \text{ V}$	6N135	CTR	5			%
		6N136	CTR	15			%

SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
High to low	$I_F = 16 \text{ mA}$ , $V_{CC} = 5.0 \text{ V}$ , $R_L = 4.1 \text{ k}\Omega$	6N135	$t_{PHL}$		0.3	1.5	$\mu\text{s}$
	$I_F = 16 \text{ mA}$ , $V_{CC} = 5.0 \text{ V}$ , $R_L = 1.9 \text{ k}\Omega$	6N136	$t_{PHL}$		0.2	0.8	$\mu\text{s}$
Low to high	$I_F = 16 \text{ mA}$ , $V_{CC} = 5.0 \text{ V}$ , $R_L = 4.1 \text{ k}\Omega$	6N135	$t_{PLH}$		0.3	1.5	$\mu\text{s}$
	$I_F = 16 \text{ mA}$ , $V_{CC} = 5.0 \text{ V}$ , $R_L = 1.9 \text{ k}\Omega$	6N136	$t_{PLH}$		0.2	0.8	$\mu\text{s}$

COMMON MODE TRANSIENT IMMUNITY							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
High	$I_F = 0 \text{ mA}$ , $V_{CM} = 10 \text{ V}_{P-P}$ , $V_{CC} = 5.0 \text{ V}$ , $R_L = 4.1 \text{ k}\Omega$	6N135	$ CM_H $		1000		$\text{V}/\mu\text{s}$
	$I_F = 0 \text{ mA}$ , $V_{CM} = 10 \text{ V}_{P-P}$ , $V_{CC} = 5.0 \text{ V}$ , $R_L = 1.9 \text{ k}\Omega$	6N136	$ CM_H $		1000		$\text{V}/\mu\text{s}$
Low	$I_F = 16 \text{ mA}$ , $V_{CM} = 10 \text{ V}_{P-P}$ , $V_{CC} = 5.0 \text{ V}$ , $R_L = 4.1 \text{ k}\Omega$	6N135	$ CM_L $		1000		$\text{V}/\mu\text{s}$
	$I_F = 16 \text{ mA}$ , $V_{CM} = 10 \text{ V}_{P-P}$ , $V_{CC} = 5.0 \text{ V}$ , $R_L = 1.9 \text{ k}\Omega$	6N136	$ CM_L $		1000		$\text{V}/\mu\text{s}$

SAFETY AND INSULATION RATINGS							
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Climatic classification (according to IEC 68 part 1)				55/100/21			
Comparative tracking index		CTI	175		399		
$V_{IOTM}$			8000				V
$V_{IORM}$			890				V
$P_{SO}$					500		mW
$I_{SI}$					300		mA
$T_{SI}$					175		$^{\circ}\text{C}$
Creepage distance	standard DIP-8		7				mm
Clearance distance	standard DIP-8		7				mm
Creepage distance	400 mil DIP-8		8				mm
Clearance distance	400 mil DIP-8		8				mm

**Note**

As per IEC 60747-5-2, § 7.4.3.8.1, this optocoupler is suitable for "safe electrical insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of protective circuits.

**TYPICAL CHARACTERISTICS**
 $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified


Fig. 1 - LED Forward Current vs. Forward Voltage

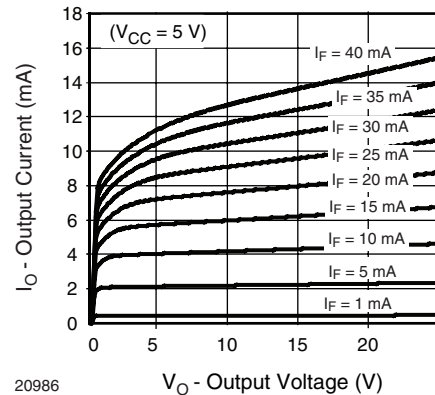


Fig. 4 - Output Current vs. Output Voltage

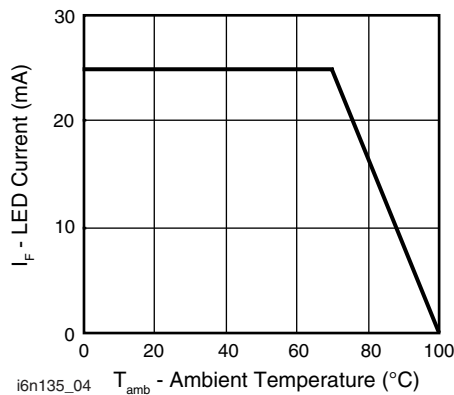


Fig. 2 - Permissible Forward LED Current vs. Temperature

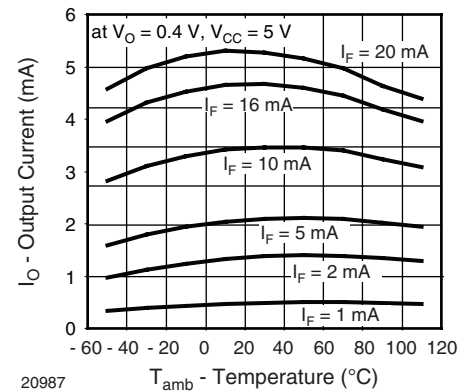


Fig. 5 - Output Current vs. Temperature

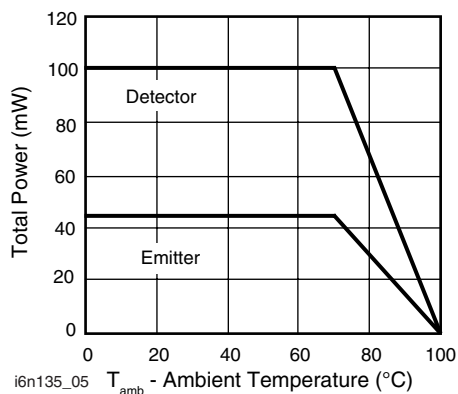


Fig. 3 - Permissible Power Dissipation vs. Temperature

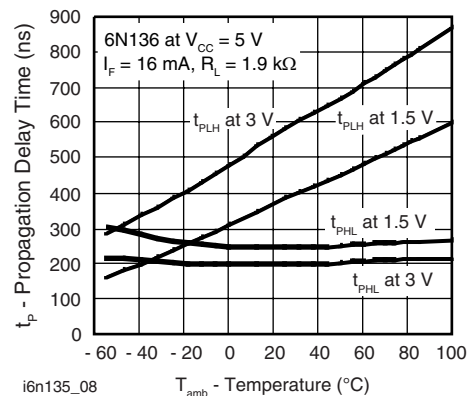


Fig. 6 - Propagation Delay vs. Ambient Temperature



Fig. 7 - Propagation Delay vs. Ambient Temperature



Fig. 9 - Small Signal Current Transfer Ratio vs. Quiescent Input Current



Fig. 8 - Logic High Output Current vs. Temperature

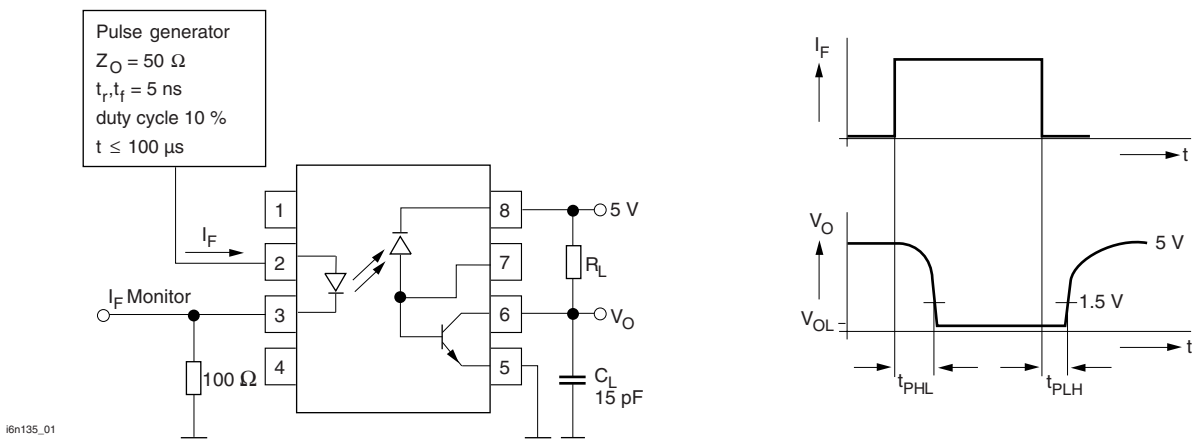


Fig. 10 - Switching Times

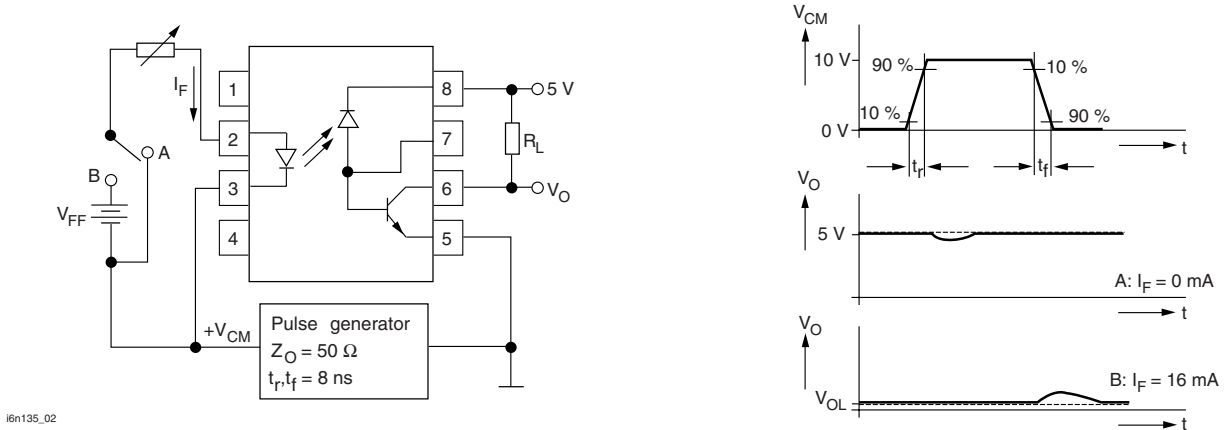
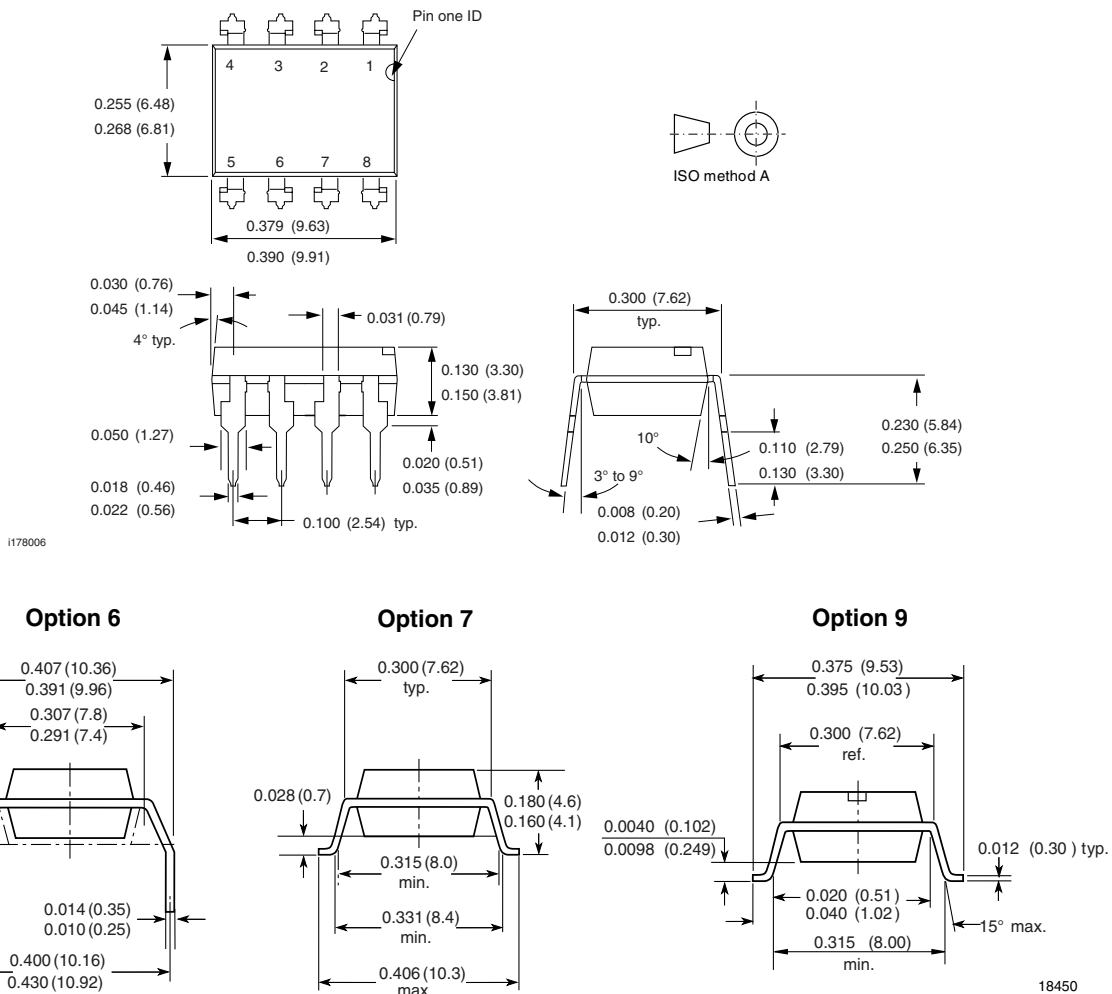


Fig. 11 - Common-Mode Interference Immunity

### PACKAGE DIMENSIONS in inches (millimeters)



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3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

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Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



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### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

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